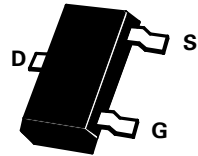


SOT23 P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – SEPTEMBER 1995

BSS84

PARTMARKING DETAIL — SP



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-50	V
Continuous Drain Current	I_D	-130	mA
Pulsed Drain Current	I_{DM}	-520	mA
Gate-Source Voltage Peak	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{TOT}	360	mW
Operating and Storage Temperature Range	$t_j; t_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-50			V	$V_{GS}=0V, I_D=0.25mA$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-0.8	-1.5	-2.0	V	$V_{DS}=V_{GS}, I_D=-1mA$
Zero gate Voltage Drain Current	I_{DSS}		-1 -2	-15 -60	μA μA	$T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$ $V_{DS}=-50V, V_{GS}=0V(2)$
				-100		$T_j=25^\circ\text{C}$ $V_{DS}=-25V, V_{GS}=0V$
Gate-Source Leakage Current	I_{GSS}		-1	-10	nA	$V_{GS} = \pm 20V$ $V_{DS}=0V$
Drain Source On-State Resistance (1)	$R_{DS(on)}$		6	10	Ω	$V_{GS}=-5V$ $I_D=-100mA$
Forward Transconductance (1) (2)	g_{fs}	0.05	0.07		S	$V_{DS}=-25V$ $I_D=-100mA$
Input Capacitance (2)	C_{iss}		40		pF	$V_{GS}=0V$ $V_{DS}=-25V$ $f=1MHz$
Output Capacitance	C_{oss}		15			
Reverse Transfer Capacitance (2)	C_{rss}		6			
Turn-On Time t_{on}	$td(on)$		10		ns	$V_{DD}=-30V$ $I_D=-0.27A$ $V_{GS}=-10V$ $R_{GS}=50\Omega$
	t_r		10			
Turn-Off Time t_{off}	$t_{d(off)}$		18			
	t_f		25			

* (1) Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle 2%
(2) Sample test.